



60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(on)}	I _D T _A = +25°C	
-60V	$125m\Omega @ V_{GS}=-10V$	-4.3A	
-007	190mΩ @ V _{GS} = -4.5V	-3.5A	

Description

This MOSFET is designed to minimize the on-state resistance yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

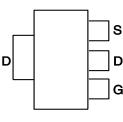
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.112 grams (Approximate)

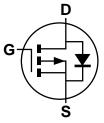


SOT223

Top View



Pin Out—Top View



Equivalent Circuit

Ordering Information (Notes 4 & 5)

Part Number	Compliance	Case	Packaging
ZXMP6A17GQTA	Automotive	SOT223	1000/Tape & Reel
ZXMP6A17GQTC	Automotive	SOT223	4000/Tape & Reel

EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

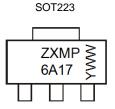
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, see http://www.diodes.com/products/packages.html.

Marking Information

Notes:



 $\begin{array}{l} \mbox{ZXMP6A17} = \mbox{Product Type Marking Code} \\ \mbox{YWW} = \mbox{Date Code Marking} \\ \mbox{Y or } \overrightarrow{Y} = \mbox{Year (ex: 8 = 2018)} \\ \mbox{WW or } \overrightarrow{WW} = \mbox{Week (01 - 53)} \end{array}$



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-60	V	
Gate-Source Voltage		V _{GS}	±20	V	
		(Note 7)		-4.3	
Continuous Drain Current	$V_{GS} = 10V$	T _A = +70°C (Note 7)	I _D	-3.5	А
		(Note 6)		-3	
Pulsed Drain Current	$V_{GS} = 10V$	(Note 8)	I _{DM}	-13.7	А
Continuous Source Current	(Body Diode)	(Note 7)	Is	-4.8	A
Pulsed Source Current (Body Diode) (Note 8)		(Note 8)	I _{SM}	-13.7	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	D	2 16		
Linear Derating Factor	(Note 7)		3.9 31	mW/°C	
Thermal Desistance Junction to Ambient	(Note 6)	D	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{OJA}	32		
Thermal Resistance, Junction to Lead	(Note 9)	R _{ƏJL}	9.8		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Notes: 6. For a device surface mounted on 25mm × 25mm × 1.6mm FR4 PCB with high coverage of single-sided 1oz copper. In still air conditions; the device is measured when operating in a steady-state condition.

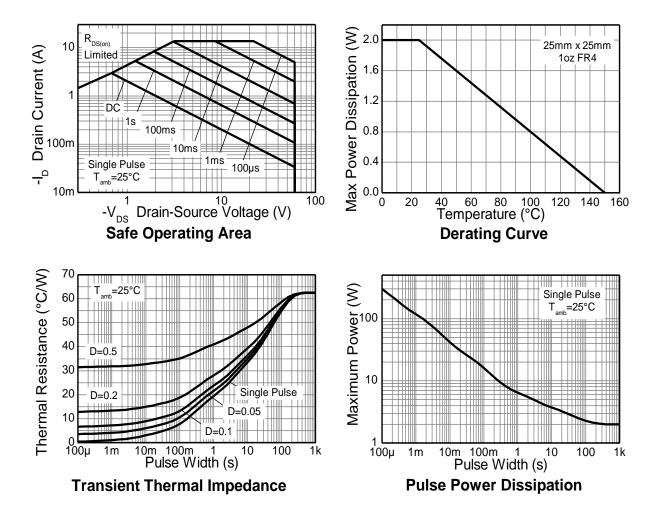
7. Same as Note 6 except the device is measured at t \leq 10s.

8. Same as Note 6 except the device is pulsed with D = 0.02 and pulse width of 300µs. The pulse current is limited by the maximum junction temperature.

9. Thermal resistance from junction to solder point (at the end of the drain lead).



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

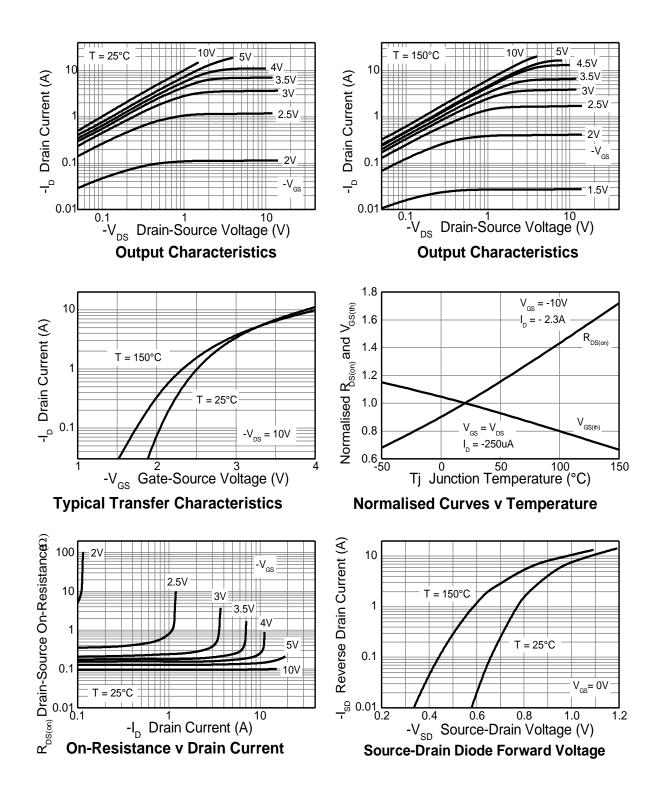
Characteristic	Symbol	Min	Тур	Max	Unit	Test	Condition
OFF CHARACTERISTICS			•	•			
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	_	V	$I_D = -250 \mu A$, $V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	-0.5	μA	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	-1	_	_	V	$I_D = -250 \mu A, V$	$_{\rm DS}$ = $V_{\rm GS}$
Static Drain-Source On-Resistance (Note 10)	P		0.096	0.125	Ω	V_{GS} = -10V, I_D	= -2.2A
	R _{DS(ON)}	_	0.12	0.19	12	V_{GS} = -4.5V, I_{D}) = -1.8A
Forward Transconductance (Notes 10 & 11)	g fs	_	4.7	_	S	V_{DS} = -15V, I_D	= -2.2A
Diode Forward Voltage (Note 10)	V _{SD}	_	-0.85	-0.95	V	$I_{S} = -2A, V_{GS} = 0V, T_{J} = +25^{\circ}C$	
Reverse Recovery Time (Note 11)	t _{rr}		25.1	_	ns	$I_{S} = -1.7A$, di/dt = 100A/µs, $T_{J} = +25$ °C	
Reverse Recovery Charge (Note 11)	Qrr	_	27.2	_	nC		
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	Ciss	_	637	_	pF	$V_{DS} = -30V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	70	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	53	—	pF		
Total Gate Charge (Note 12)	Qg	_	9	_	nC	$V_{GS} = -4.5V$	
Total Gate Charge (Note 12)	Qg	_	17.7	_	nC	V _{DS} = -30V	
Gate-Source Charge (Note 12)	Q _{gs}	_	1.6	_	nC	V _{GS} = -10V	I _D = -2.2A
Gate-Drain Charge (Note 12)	Q _{gd}	_	4.4	_	nC		
Turn-On Delay Time (Note 12)	t _{D(on)}	_	2.6	_	ns		
Turn-On Rise Time (Note 12)	tr	_	3.4	_	ns	$V_{DD} = -30V, V_{GS} = -10V$ $I_D = -1A, R_G \cong 6\Omega$	
Turn-Off Delay Time (Note 12)	t _{D(off)}	_	26.2		ns		
Turn-Off Fall Time (Note 12)	t _f	_	11.3	_	ns		

10. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%. 11. For design aid only—not subject to production testing. 12. Switching characteristics are independent of operating junction temperatures.

Notes:

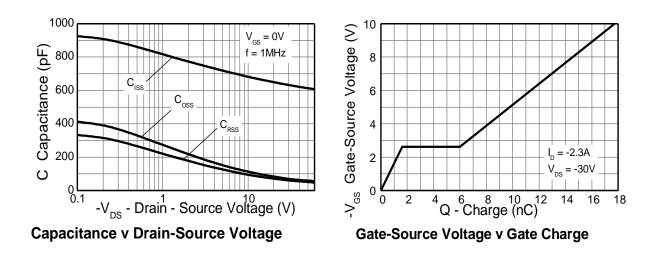


Typical Characteristics

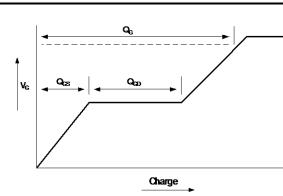




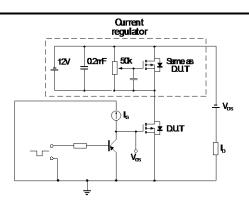
Typical Characteristics (continued)



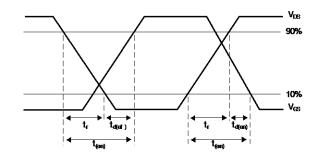
Test Circuits



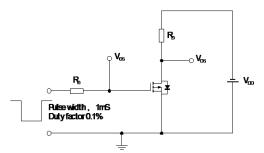
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

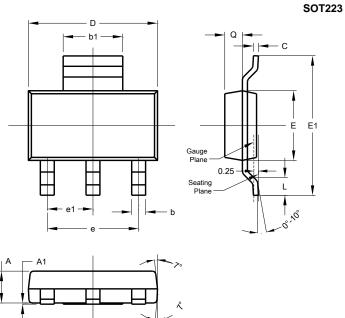






Package Outline Dimensions

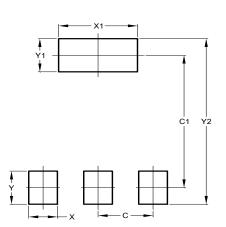
Please see http://www.diodes.com/package-outlines.html for the latest version.



1					
SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	4.60				
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All [All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223

Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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